L Number	Hits	Search Text	DB	Time stamp
-	111	(thin adj film adj transistor\$1 tft) with (sensor\$3 and	USPAT;	2004/10/29 11:00
		switch\$3) same capacitor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	6	5895936.URPN.	USPAT	2004/10/29 08:54
-	9	("5003356"   "5032883"   "5313066"   "5319206"	USPAT	2004/10/29 08:54
	_	"5352897"   "5396072"   "5463225"   "5498880"		• •
		"5563421").PN.		
_	118	(thin adj film adj transistor\$1 tft) with (sensor\$3 and	USPAT;	2004/10/29 09:39
	110	switch\$3) and (memory capacitor) and ohmic	US-PGPUB;	200 1, 20, 25 05 105
		Switchips) and (memory capacitor) and omine	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	111	(thin adj film adj transistort1 tf) with (concort2 and	USPAT;	2004/10/29 09:40
-	111	(thin adj film adj transistor\$1 tft) with (sensor\$3 and		2004/10/23 03.40
		switch\$3) same capacitor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/40/20 00 40
-	80	((thin adj film adj transistor\$1 tft) with (sensor\$3 and	USPAT;	2004/10/29 09:40
		switch\$3) and (memory capacitor) and ohmic) not ((thin adj	US-PGPUB;	
		film adj transistor\$1 tft) with (sensor\$3 and switch\$3) same	EPO; JPO;	
		capacitor )	DERWENT;	
			IBM_TDB	
-	3	(thin adj film adj transistor\$1 tft) with (sensor\$3 and	USPAT;	2004/10/29 11:01
		access\$3) same capacitor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		•	IBM_TDB	
-	3	(thin adj film adj transistor\$1 tft) with (sensor\$3 and	USPAT;	2004/10/29 11:01
		acces\$3) same capacitor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4	(thin adj film adj transistor\$1 tft) with (sensor\$3 and	USPAT;	2004/10/29 11:44
	1	access\$3) and capacitor not ((thin adj film adj transistor\$1	US-PGPUB;	
•		tft) with (sensor\$3 and access\$3) same capacitor)	EPO; JPO;	
		,,,,,,,,,	DERWENT;	
			IBM_TDB	
_	2	("5466620").PN.	USPAT;	2004/10/29 11:50
	_	,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
	2	("5436182").PN.	USPAT;	2004/10/29 11:50
_	_	( 5 150102 ) N.	US-PGPUB;	200 1/20/25 22120
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	•
	4226	(357/50 52 54 57 194 197) CCLS	USPAT;	2004/10/29 13:38
-	4236	(257/59,53,54,57,184,187).CCLS.	US-PGPUB;	2007/10/23 13.30
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/40/20 42:22
-	1819	(tft thin near film near transistor) and	USPAT;	2004/10/29 13:38
		((257/59,53,54,57,184,187).CCLS.)	US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
	l		IBM_TDB	_

•				-
-	821	((tft thin near film near transistor) and	USPAT;	2004/10/29 13:38
		((257/59,53,54,57,184,187).CCLS.)) and (capacitor	US-PGPUB;	
		memory)	EPO; JPO;	
		,	DERWENT;	
,			IBM_TDB	
_	587	(tft thin near film near transistor) same switch\$3 and (((tft	USPAT;	2004/10/29 13:39
	557	thin near film near transistor) and	US-PGPUB;	
		((257/59,53,54,57,184,187).CCLS.)) and (capacitor	EPO; JPO;	
		memory))	DERWENT;	
		memory))	IBM_TDB	
_	571	(tft thin near film near transistor) with switch\$3 and (((tft	USPAT;	2004/10/29 13:39
-	3/1	thin near film near transistor) and	US-PGPUB;	200 1/10/25 13.55
		((257/59,53,54,57,184,187).CCLS.)) and (capacitor	EPO; JPO;	
			DERWENT;	
		memory))	IBM_TDB	
	-11	(Affi this name film name translator) approx quitable? and ((/Aff	USPAT;	2004/10/29 13:47
-	511	(tft thin near film near transistor) near3 switch\$3 and (((tft		2004/10/29 13.47
1		thin near film near transistor) and	US-PGPUB;	
		((257/59,53,54,57,184,187).CCLS.)) and (capacitor	EPO; JPO;	
		memory))	DERWENT;	
			IBM_TDB	2004/40/20 44 40
-	24		USPAT;	2004/10/29 14:19
		((257/59,53,54,57,184,187).CCLS.)) and (capacitor	US-PGPUB;	,
		memory)) and dual near3 electrode	EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
	16	(((tft thin near film near transistor) same (capacitor	USPAT;	2004/10/29 14:24
		memory) and ((257/59,53,54,57,184,187).CCLS.)) ) and	US-PGPUB;	
		dual near3 electrode	EPO; JPO;	
			DERWENT;	
		, , , , , , , , , , , , , , , , , , ,	IBM_TDB	
-	31	(((tft thin near film near transistor) same (capacitor	USPAT;	2004/10/29 14:30
		memory) and (438/\$6 257/\$6)) ) and dual near3 electrode	US-PGPUB;	
		not ((((tft thin near film near transistor) same (capacitor	EPO; JPO;	
	ĺ	memory) and ((257/59,53,54,57,184,187).CCLS.)) ) and	DERWENT;	
	1	dual near3 electrode)	IBM_TDB	
	52	(((tft thin near film near transistor) same (capacitor	USPAT;	2004/10/29 14:34
		memory) and (438/\$6 257/\$6)) ) and dual near4 electrode	US-PGPUB;	
		not ((((tft thin near film near transistor) same (capacitor	EPO; JPO;	
		memory) and ((257/59,53,54,57,184,187).CCLS.)) ) and	DERWENT;	
		dual near3 electrode)	IBM_TDB	
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